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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/690,507	10/23/2003	Ji Yong Park	1514.1032	6043
49455	7590 04/18/2006		EXAMINER	
STEIN, MCEWEN & BUI, LLP			SONG, MATTHEW J	
1400 EYE ST SUITE 300	IREEI, NW		ART UNIT	PAPER NUMBER
WASHINGT	ON, DC 20005		1722	
			DATE MAILED: 04/18/2000	5

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	í.
	10/690,507	PARK ET AL.	
Office Action Summary	Examiner	Art Unit	
	Matthew J. Song	1722	
The MAILING DATE of this communication Period for Reply	appears on the cover sheet w	th the correspondence address	
A SHORTENED STATUTORY PERIOD FOR RE WHICHEVER IS LONGER, FROM THE MAILING  - Extensions of time may be available under the provisions of 37 CFF after SIX (6) MONTHS from the mailing date of this communication.  - If NO period for reply is specified above, the maximum statutory period for reply within the set or extended period for reply will, by stany reply received by the Office later than three months after the meanned patent term adjustment. See 37 CFR 1.704(b).	B DATE OF THIS COMMUNION R 1.136(a). In no event, however, may a control of the c	CATION.  eply be timely filed  ITHS from the mailing date of this communication.  BANDONED (35 U.S.C. § 133).	
Status			
1) Responsive to communication(s) filed on 1	7 January 2006.		
2a) This action is <b>FINAL</b> . 2b) ⊠ 1	This action is non-final.		
3) Since this application is in condition for allo	wance except for formal matt	ers, prosecution as to the merits is	
closed in accordance with the practice und	er <i>Ex par</i> te <i>Quayl</i> e, 1935 C.D	. 11, 453 O.G. 213.	
Disposition of Claims			
4) Claim(s) 1-15 is/are pending in the applicat	ion.		
4a) Of the above claim(s) 4,5,11,12 and 15	is/are withdrawn from consid	eration.	
5) Claim(s) is/are allowed.	\\		
6)⊠ Claim(s) <u>1-3,6-10,13 and 14</u> is/are rejected	•		
7) Claim(s) is/are objected to.			
8) Claim(s) are subject to restriction an	d/or election requirement.		
Application Papers	•		
9)☐ The specification is objected to by the Exam	niner.		
10) The drawing(s) filed on is/are: a)	accepted or b)☐ objected to	by the Examiner.	
Applicant may not request that any objection to	the drawing(s) be held in abeyar	ice. See 37 CFR 1.85(a).	
Replacement drawing sheet(s) including the cor	•		).
11) The oath or declaration is objected to by the	Examiner. Note the attached	d Office Action or form PTO-152.	
Priority under 35 U.S.C. § 119			
12)⊠ Acknowledgment is made of a claim for fore	eign priority under 35 U.S.C. §	119(a)-(d) or (f).	
a)⊠ All b)□ Some * c)□ None of:			
1. Certified copies of the priority docum	ents have been received.		•
2. Certified copies of the priority docum	ents have been received in A	pplication No	
<ol><li>Copies of the certified copies of the p</li></ol>	priority documents have been	received in this National Stage	
application from the International Bur			
* See the attached detailed Office action for a	list of the certified copies not	received.	•
Attachment(s)			
<ol> <li>Notice of References Cited (PTO-892)</li> <li>Notice of Draftsperson's Patent Drawing Review (PTO-948)</li> </ol>		Summary (PTO-413) s)/Mail Date	
<ol> <li>Notice of Draftsperson's Patent Drawing Review (P10-948)</li> <li>Information Disclosure Statement(s) (PTO-1449 or PTO/SB. Paper No(s)/Mail Date 10/23/03.</li> </ol>		nformal Patent Application (PTO-152)	

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**DETAILED ACTION** 

Election/Restrictions

1. Applicant's election with traverse of Group I, claims 1-3, 6-10 and 13-14 in the reply filed

on 1/17/2006 is acknowledged. The traversal is on the ground(s) that there would be no undue

burden on the Examiner in examining both the method and product because they are in the same

field of technology. This is not found persuasive because a serious burden exists in the differing

issues likely to arise during the prosecution of the different statutory classes of invention.

The requirement is still deemed proper and is therefore made FINAL.

2. Claims 4-5, 11-12 and 15 are withdrawn from further consideration pursuant to 37 CFR

1.142(b), as being drawn to a nonelected invention, there being no allowable generic or linking

claim. Applicant timely traversed the restriction (election) requirement in the reply filed on

1/17/2006.

Claim Objections

3. Claim 1 is objected to because of the following informalities: In line 3, "crystallizing" is

spelled "crystallizaing", which is incorrect. Appropriate correction is required.

Claim Rejections - 35 USC § 112

4. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode

contemplated by the inventor of carrying out his invention.

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5. Claim 8 recites the limitation "wherein an overlapping irradiated width of the thin film is larger than 0.5 μm" in line 2. There is insufficient antecedent basis for this limitation in the claim. Claim 8 depends from claim 6, which does not recite an overlapping width.

## Claim Rejections - 35 USC § 102

6. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

7. Claims 1-3 are rejected under 35 U.S.C. 102(e) as being anticipated by Yang (US 2002/0197759 A1).

Yang teaches a method of sequential laser solidification (SLS) for crystallization of amorphous silicon. Yang also teaches the makes moves transversely by no more than the wide of the shaped patterns as a laser performs SLS crystallization. (Abstract). Yang also teaches a mask includes a plurality of slits A that pass a laser beam and a light absorptive areas B that absorb the laser beam and the wide of each slit A defines the grain size of the crystallized silicon ([0010]). Yang also teaches using a pattern of 2 μm ([0072]) and grains of 1-1.5 μm ([0076]), this reads on applicant's overlappingly irradiating the laser beam onto a region wider than 0.5 μm. Yang also teaches an overlapped regions ([0040]). Yang also teaches moving the substrate 0.75 μm (Table 1).

8. Claims 1-3 and 13 are rejected under 35 U.S.C. 102(b) as being anticipated by jung (US 2002/0182341 A1).

In a method of crystallizing silicon, note entire reference, Jung discloses a method of using a laser beam having a width of 1-3 millimeters and an overlapping ratio of 90% is suitable ([0022]), this reads on applicant's overlapping width is greater than 0.5 μm because 90% of 1 mm is larger than 0.5 µm. Jung also discloses sequential laser solidification (SLS) ([0019]).

## Claim Rejections - 35 USC § 103

- 9. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

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10. Claims 6-10, 13-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yang (US 2002/0197759 A1) as applied to claims 1 and 3 above.

Yang teaches a method of sequential laser solidification (SLS) for crystallization of amorphous silicon. Yang also teaches the makes moves transversely by no more than the wide of the shaped patterns as a laser performs SLS crystallization. (Abstract). Yang also teaches a mask includes a plurality of slits A that pass a laser beam and a light absorptive areas B that absorb the laser beam and the wide of each slit A defines the grain size of the crystallized silicon ([0010]). Yang also teaches using a pattern of 2 μm ([0072]) and grains of 1-1.5 μm ([0076]), this reads on applicant's overlappingly irradiating the laser beam onto a region wider than 0.5 μm. Yang also teaches an overlapped regions ([0040]). Yang also teaches more rapid crystallization can be achieved using masks having different slit patterns and laser ([0035]). Yang also teaches a pattern where the slit patterns are wider than an interval "O". (Fig 6 and [0035]).

Yang does not teach a mask with a laser transmission region that is wider than a laser non-transmission region by more than 1  $\mu$ m and the claimed amount of overlap.

Yang teaches using different patterns and a pattern where the laser transmission region is larger than a non-transmission regions. It would have been obvious to a person of ordinary skill in the art at the time of the invention to modify Yang having a transmission region that is wider than a non-transmission region by more an 1 µm and with an overlap of larger an 0.5 µm by optimizing the mask size because the size of the slit is a result effective and different patterns are used to achieve more rapid crystallization. Furthermore, changes in size are held to obvious, absent evidence of unexpected results. (MPEP 2144.03).

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Referring to claim 13, Yang teaches crystallized silicon particles are re-melted, this reads

on overlappingly irradiating already formed crystals.

Conclusion

11. Any inquiry concerning this communication or earlier communications from the examiner

should be directed to Matthew J. Song whose telephone number is 571-272-1468. The examiner

can normally be reached on M-F 9:00-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Yogendra Gupta can be reached on 571-272-1316. The fax phone number for the

organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Matthew J Song

Examiner

SORY PATENT EXAMINES Art Unit 1722

TECHNOLOGY CENTER 1709

MJS

April 2, 2006